

Gallium Nitride 48V, 12.5W, DC-6 GHz HEMT

Built using the SIGANTIC[®] process - A proprietary GaN-on-Silicon technology

Features

- Suitable for linear and saturated applications
- Tunable from DC-6 GHz
- 48V Operation
- Industry Standard Plastic Package
- High Drain Efficiency (>60%)



Applications

- Defense Communications
- Land Mobile Radio
- Avionics
- Wireless Infrastructure
- ISM Applications
- VHF/UHF/L/S-Band Radar

DC-6 GHz
12.5W
GaN HEMT



Product Description

The NPT2018 GaN HEMT is a wideband transistor optimized for DC-6 GHz operation. This device has been designed for CW, pulsed, and linear operation with output power levels to 12.5W (41 dBm) in an industry standard surface mount plastic package.

RF Specifications (CW, 2.5 GHz): $V_{DS} = 48V$, $I_{DQ} = 75mA$, $T_C = 25^{\circ}C$

Symbol	Parameter	Min	Typ	Max	Units
G_{SS}	Small-signal Gain	-	17.5	-	dB
P_{SAT}	Saturated Output Power	-	41.8	-	dBm
η_{SAT}	Efficiency at Saturated Output Power	-	60	-	%
G_P	Gain at $P_{OUT} = 12.5W$	-	16.5	-	dB
η	Drain Efficiency at $P_{OUT} = 12.5W$	-	55	-	%
V_{DS}	Drain Voltage	-	48	-	V
Ψ	Ruggedness: Output Mismatch, all phase angles	VSWR = 10:1, No Device Damage			

DC Specifications: $T_C = 25^\circ\text{C}$

Symbol	Parameter	Min	Typ	Max	Units
Off Characteristics					
I_{DLK}	Drain-Source Leakage Current ($V_{GS}=-8\text{V}$, $V_{DS}=160\text{V}$)	-	-	3	mA
I_{GLK}	Gate-Source Leakage Current ($V_{GS}=-8\text{V}$, $V_{DS}=0\text{V}$)	-	-	1.5	mA
On Characteristics					
V_T	Gate Threshold Voltage ($V_{DS}=48\text{V}$, $I_D=3\text{mA}$)	-2.5	-1.5	-0.5	V
V_{GSQ}	Gate Quiescent Voltage ($V_{DS}=48\text{V}$, $I_D=75\text{mA}$)	-2.1	-1.2	-0.3	V
R_{ON}	On Resistance ($V_{DS}=2\text{V}$, $I_D=22\text{mA}$)	-	1.6	-	Ω
$I_{D, MAX}$	Maximum Drain Current ($V_{DS}=7\text{V}$ pulsed, 300 μs pulse width, 0.2% Duty Cycle)	-	1.75	-	A

Thermal Resistance Specification:

Symbol	Parameter	Typ	Units
$R_{\theta JC}$	Thermal Resistance (Junction-to-Case), $T_J = 200^\circ\text{C}$	6.5	$^\circ\text{C/W}$

Junction Temperature (T_J) measured using IR Microscopy, Case Temperature (T_C) measured using a thermocouple embedded in heatsink.

Absolute Maximum Ratings: Not simultaneous, $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max	Units
V_{DS}	Drain-Source Voltage	160	V
V_{GS}	Gate-Source Voltage	-10 to 3	V
I_G	Gate Current	6	mA
P_T	Total Device Power Dissipation (Derated above 25°C)	26.9	W
T_{STG}	Storage Temperature Range	-65 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature	200	$^\circ\text{C}$
HBM	Human Body Model ESD Rating (per JESD22-A114)	Class 1A	
MSL	Moisture sensitivity level (per IPC/JEDEC J-STD-020)	TBD	

Load-Pull Data, Reference Plane at Device Leads

$V_{DS}=48V$, $I_{DQ}=75mA$, $T_C=25^\circ C$ unless otherwise noted

Optimum Source and Load Impedances:

(CW Drain Efficiency and Output Power Tradeoff Impedance)

Frequency (MHz)	$Z_S (\Omega)$	$Z_L (\Omega)$	$P_{SAT} (W)$	$G_{SS} (dB)$	Drain Efficiency @ P_{SAT} (%)
900	$8.8 + j10.3$	$31 + j36$	17	25.0	64
2500	$4.1 - j2.9$	$12.5 + j18$	16	18.0	59
4000	$4.5 - j9.5$	$7.5 + j9.4$	14	15.0	51
5800	$5.3 - j21.5$	$5.0 - j1.6$	12	13.5	45

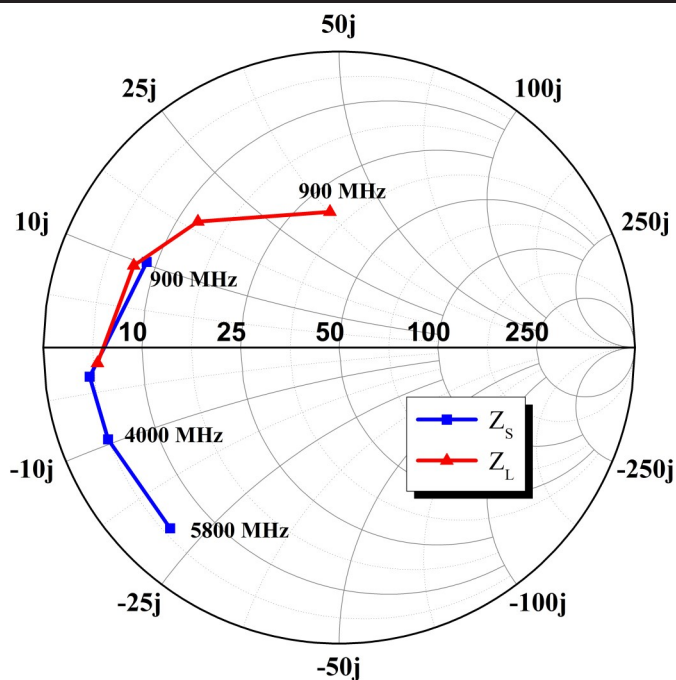
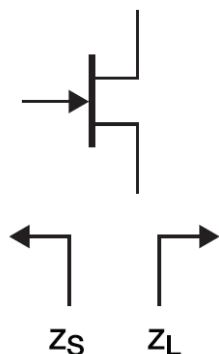


Figure 1: CW Power/Drain Efficiency Tradeoff Impedances, $Z_0=50\Omega$

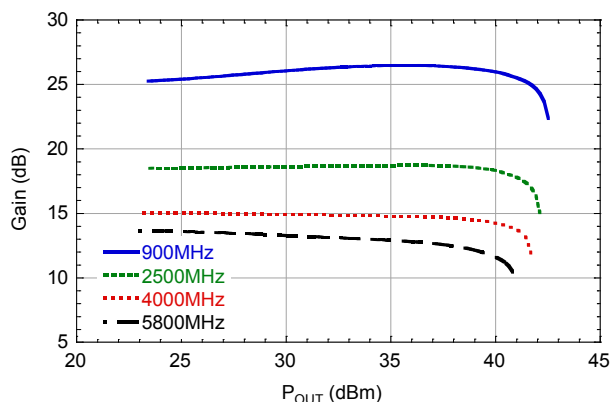


Figure 2: Gain vs. P_{OUT}

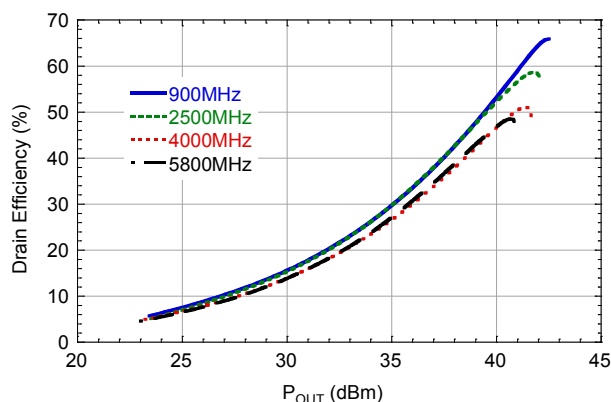


Figure 3: Efficiency vs. P_{OUT}

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Additional Information

**This part is lead-free and is compliant with the RoHS directive
(Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).**

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